



US00D777124S

(12) **United States Design Patent**  
**Hasegawa et al.**

(10) **Patent No.:** **US D777,124 S**  
(45) **Date of Patent:** **\*\* Jan. 24, 2017**

(54) **POWER SEMICONDUCTOR DEVICE**

2924/1715;H01L 2924/17151; H01L  
2924/181; H01L 2924/1811; H01L  
2924/1815; H01L 2924/19042; H01L  
2924/1905; H01L 2224/08054; H01L  
23/58; H05B 41/14; H02B 6/4201; G02B  
6/4256; G02B 6/4257; G02B  
6/4261; G02B 6/4262; G02B 6/42;  
(Continued)

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(\*\*) Term: **15 Years**

(21) Appl. No.: **29/568,598**

(22) Filed: **Jun. 20, 2016**

**Related U.S. Application Data**

(62) Division of application No. 29/503,649, filed on Sep. 29, 2014.

(30) **Foreign Application Priority Data**

Apr. 2, 2014 (JP) ..... 2014-007263  
Apr. 2, 2014 (JP) ..... 2014-007264  
Apr. 2, 2014 (JP) ..... 2014-007265  
Apr. 2, 2014 (JP) ..... 2014-007266

(51) **LOC (10) Cl.** ..... **13-03**

(52) **U.S. Cl.**  
USPC ..... **D13/182**

(58) **Field of Classification Search**  
USPC ..... D13/182  
CPC ..... H01L 21/00; H01L 21/02433; H01L 2224/42; H01L 2224/43; H01L 2021/00; H01L 2021/02; H01L 2021/04; H01L 21/4814; H01L 21/4846; H01L 21/4871; H01L 21/67144; H01L 23/12; H01L 23/13; H01L 23/14; H01L 23/147; H01L 2924/171; H01L 2924/1711; H01L

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(57) **CLAIM**

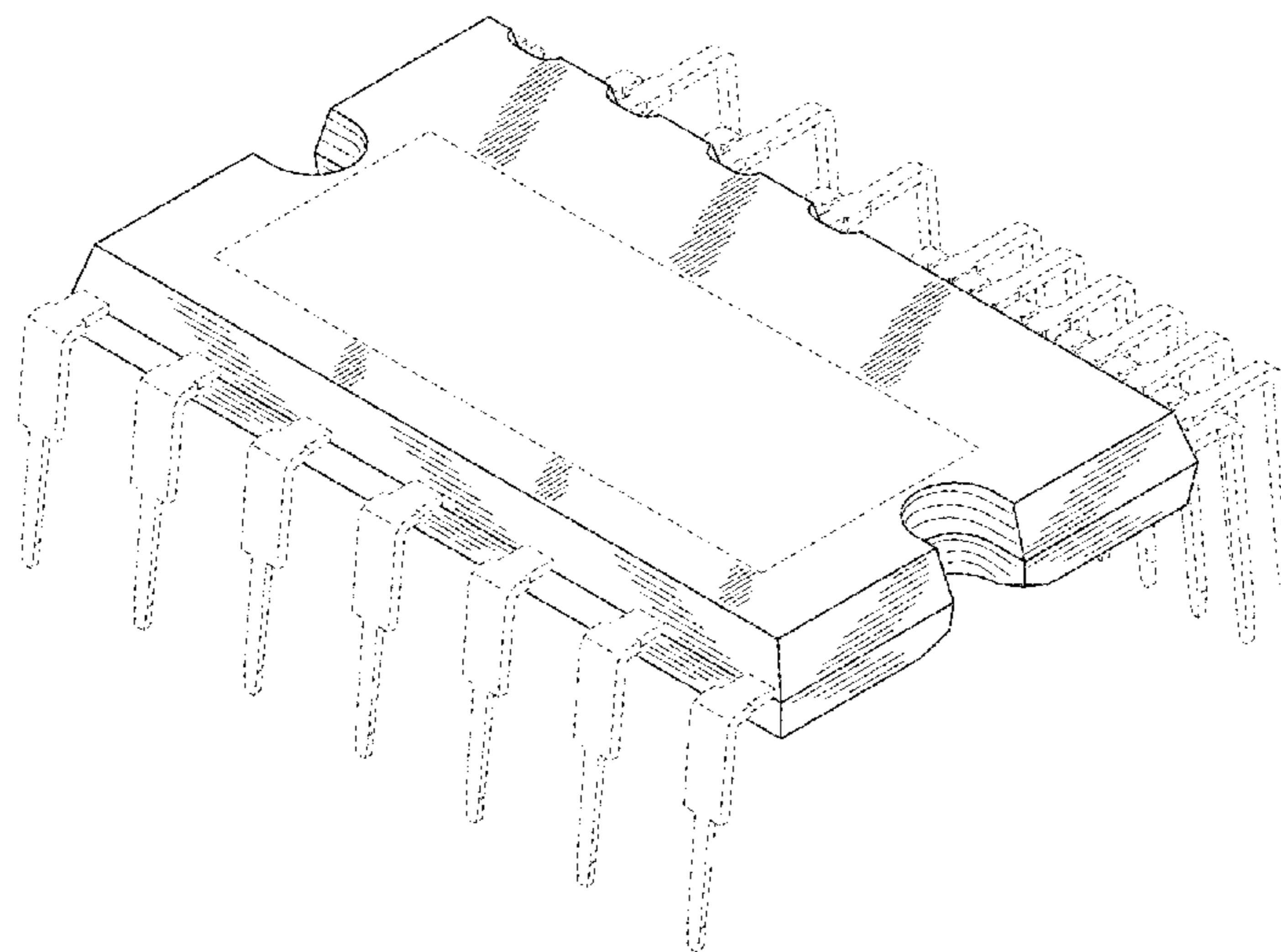
The ornamental design for a power semiconductor device, as shown and described.

**DESCRIPTION**

FIG. 1 is a front, right side, bottom perspective view of a power semiconductor device showing our new design; FIG. 2 is a rear, left side, top perspective view thereof; FIG. 3 is a front view thereof; FIG. 4 is a rear view thereof; FIG. 5 is a left side view thereof; FIG. 6 is a right side view thereof; FIG. 7 is a top plan view thereof; and, FIG. 8 is a bottom plan view thereof.

The broken lines shown represent unclaimed subject matter of a power semiconductor device and form no part of the claimed design.

**1 Claim, 8 Drawing Sheets**



(58) **Field of Classification Search**  
 CPC ..... G02B 6/4281; H05K 1/14; H05K 1/141;  
 H05K 1/142; H05K 1/144; H05K 1/18;  
 H05K 1/181; H05K 1/182; H05K 1/026;  
 H05K 1/0228; H05K 1/0245; H05K  
 1/0236; H05K 1/0263  
 See application file for complete search history.

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**FIG. 1**

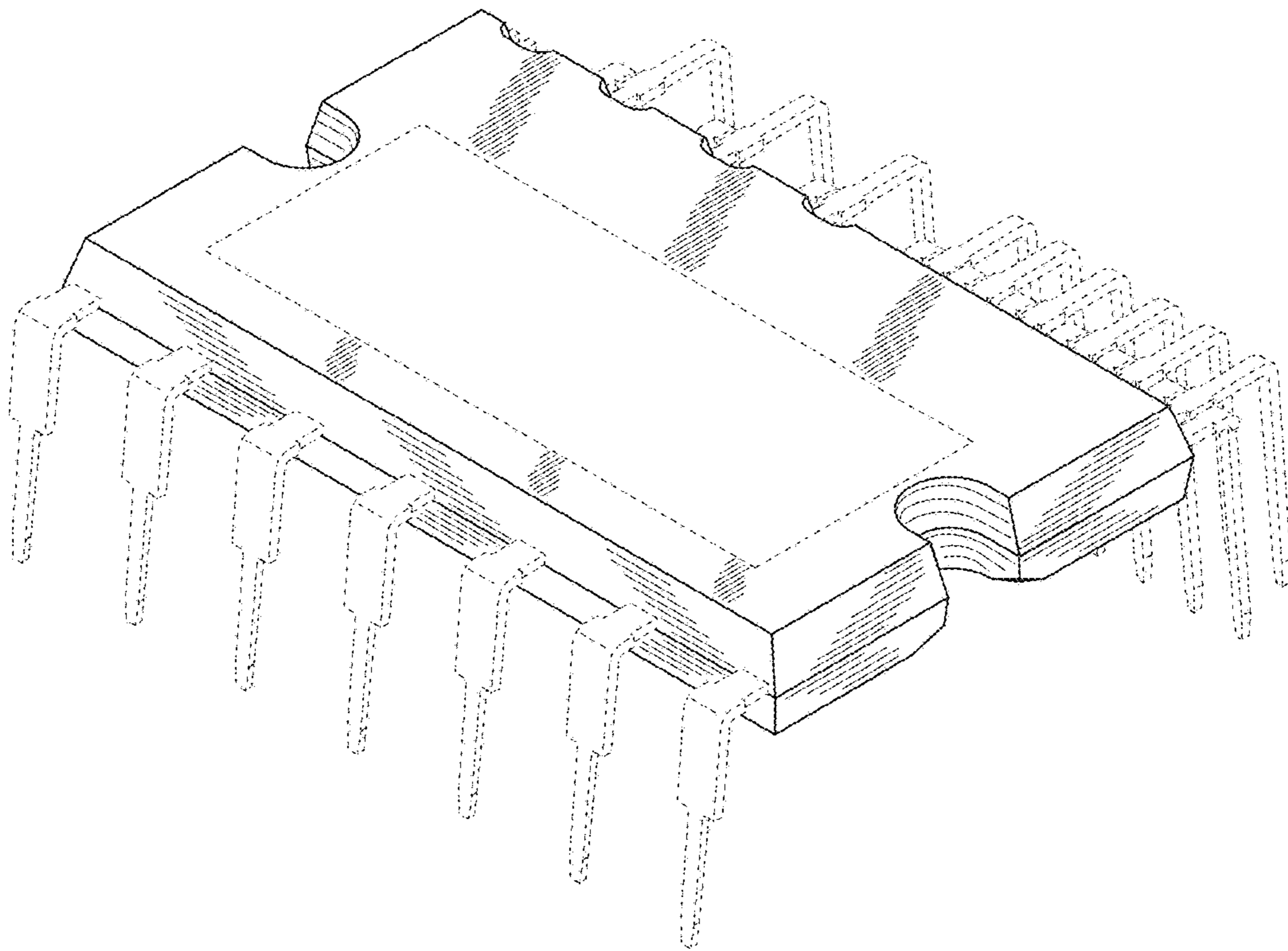
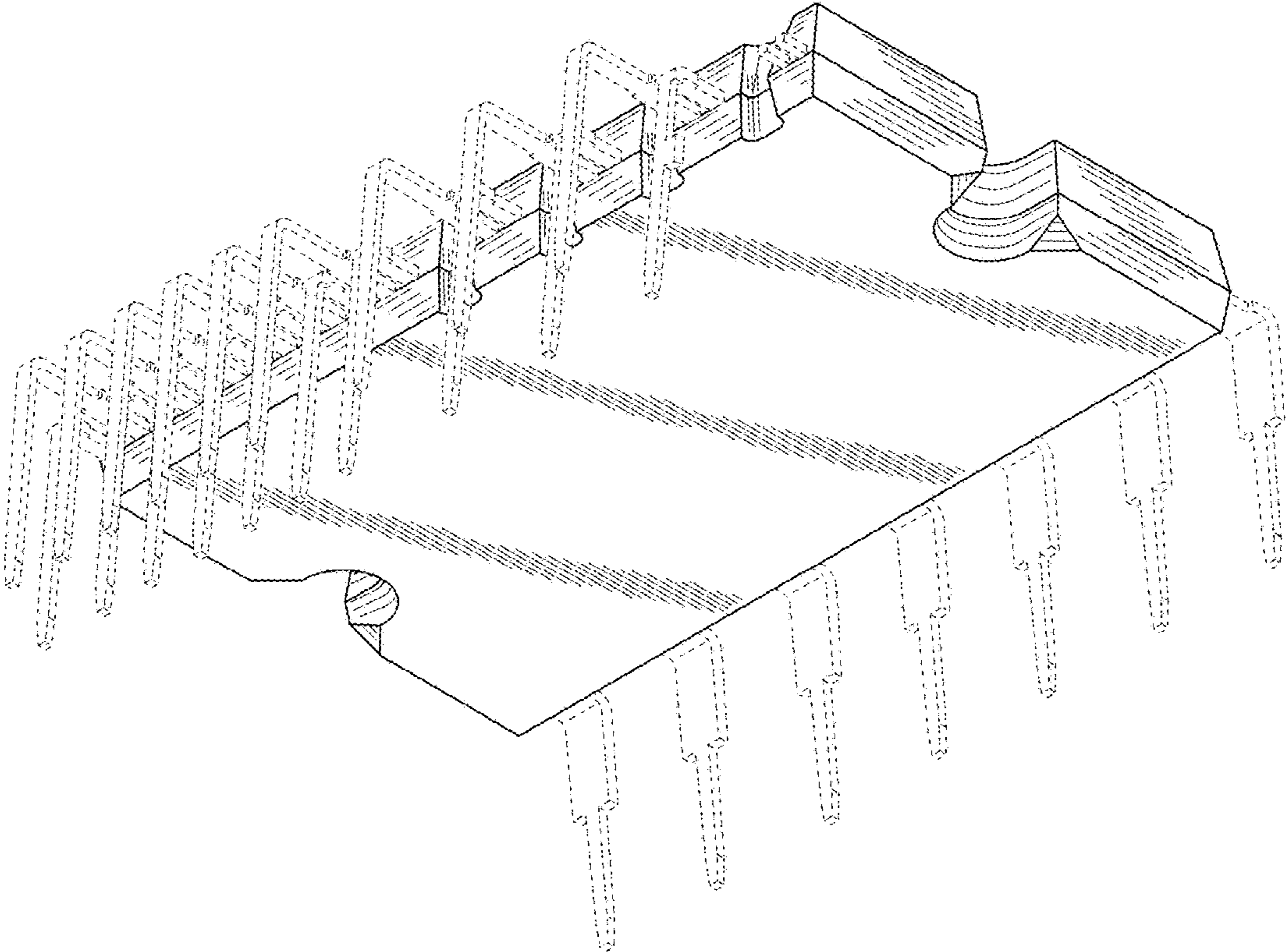


FIG. 2



**FIG. 3**

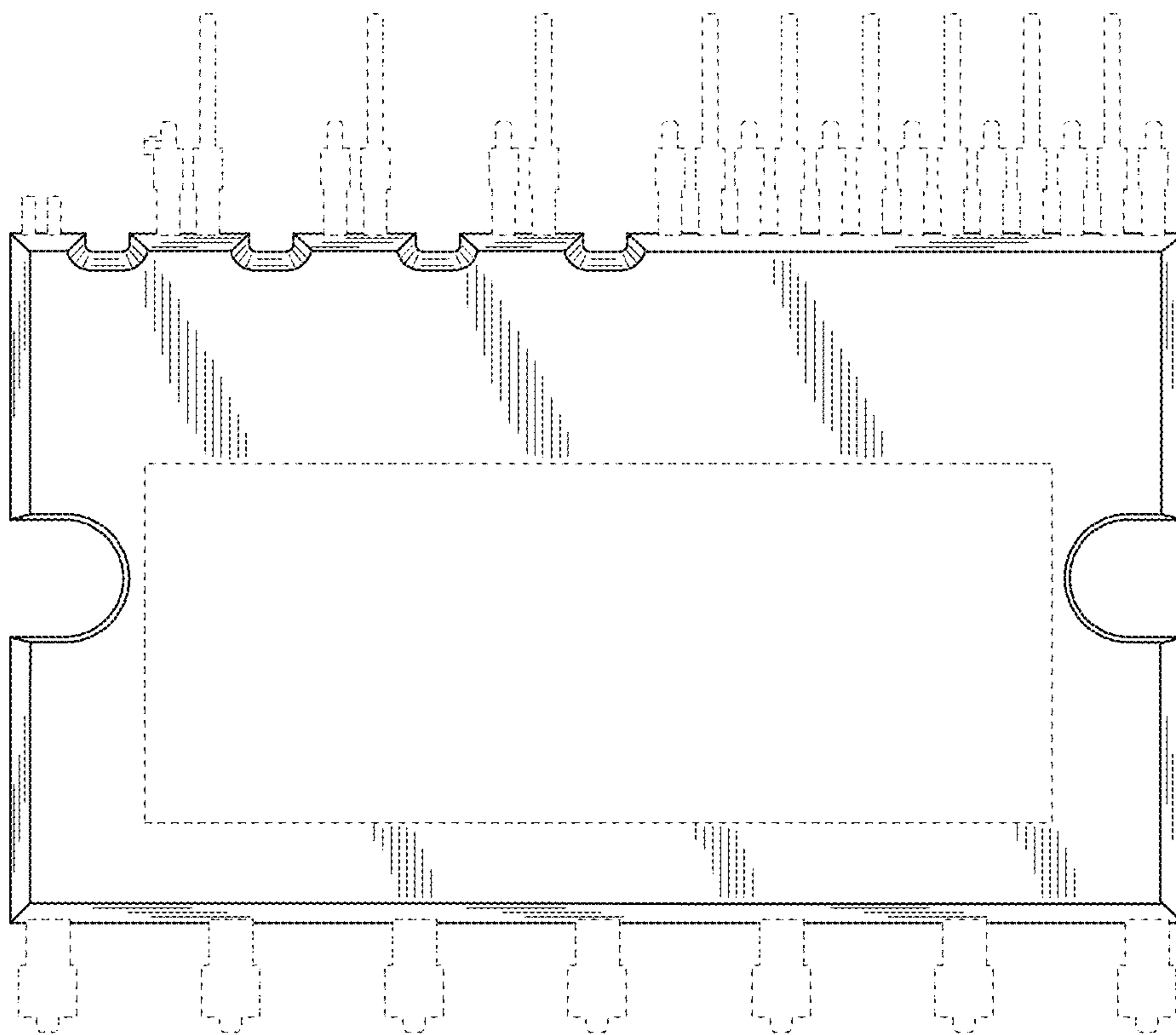


FIG. 4

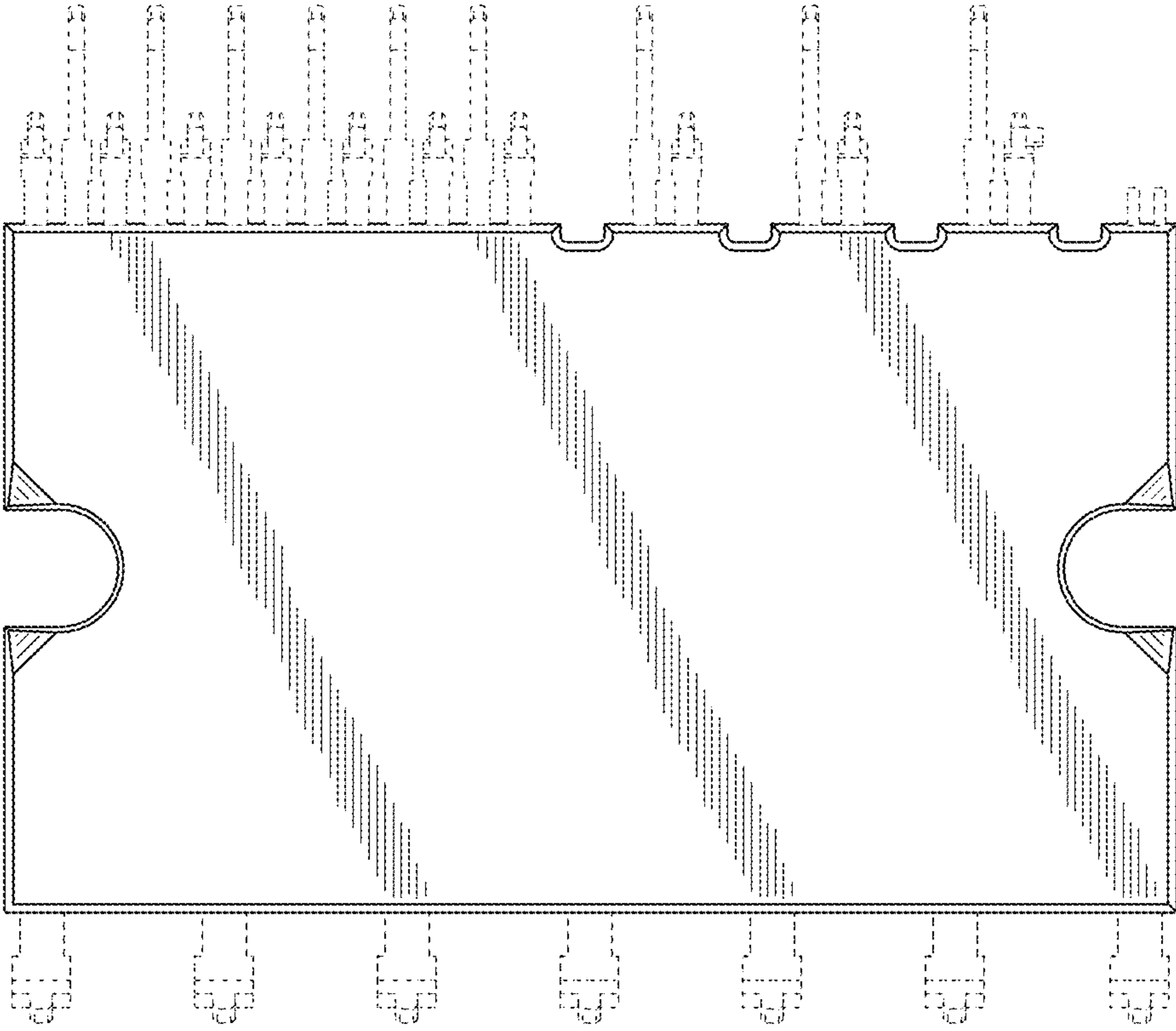


FIG. 5

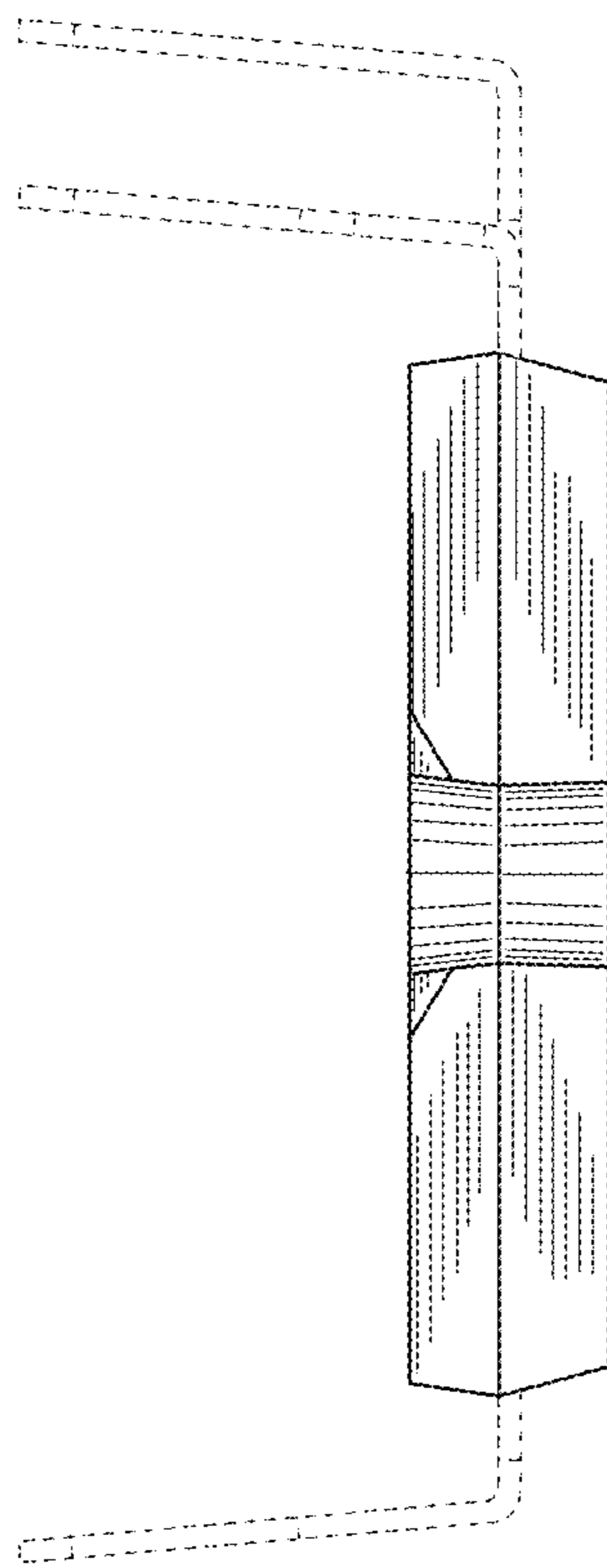


FIG. 6

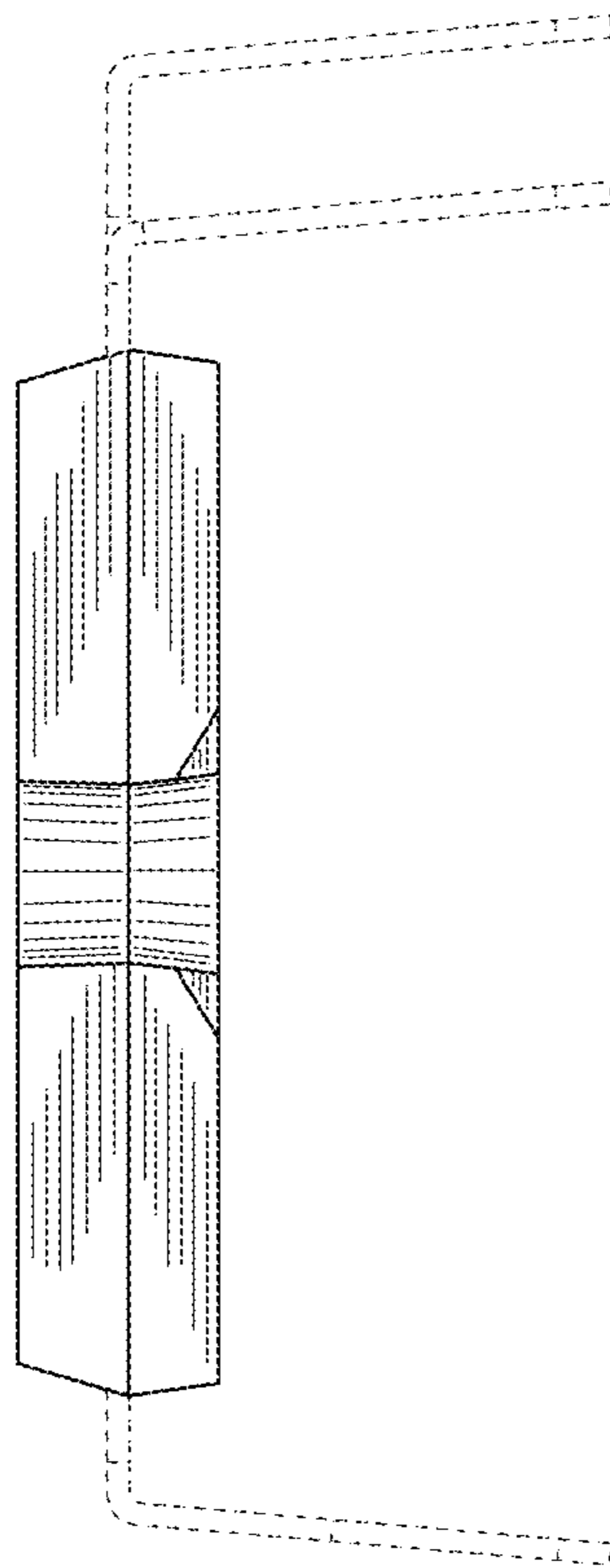




FIG. 7

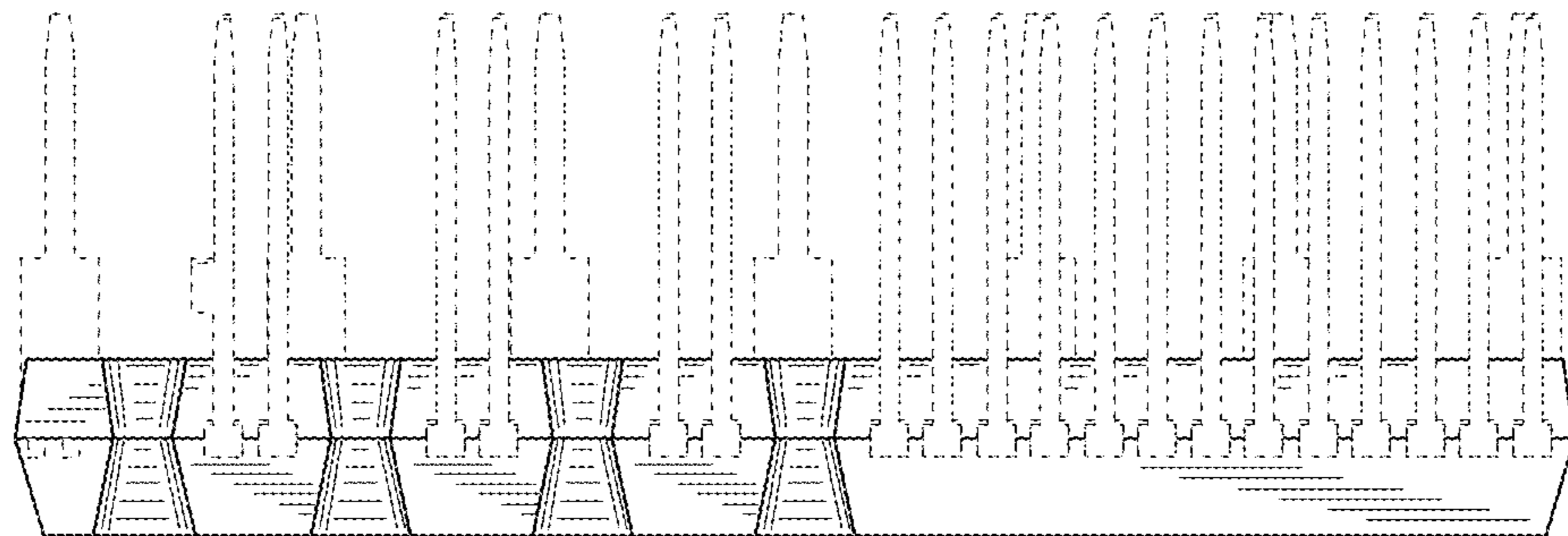


FIG. 8

